IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) Field-effect power transistor ~~having~~ comprising:
   (a) a first semiconductor region with first MOS channels having a first ratio of a channel width to a channel length for conducting through an electric current from a source terminal to a drain terminal in a manner dependent on a signal at a gate contact of the first semiconductor region;
   (b) at least one second semiconductor region with second MOS channels having a second ratio of the channel width to the channel length for conducting through an electric current from the source terminal to the drain terminal in a manner dependent on a signal at [[the]] a gate contact of the second semiconductor region;
   (c) a drive terminal for providing a drive signal at the gate contacts, a first predetermined resistor in each case being provided between the gate contact of the at least one second semiconductor region and the drive terminal; and
   (d) an overvoltage protection device being provided at least between the gate contact of the second semiconductor region and the drain terminal, said device switching on the at least one second semiconductor region if the voltage between the gate contact of the second semiconductor region and the drain terminal exceeds a predetermined value.

2. (Previously Presented) Power semiconductor according to claim 1, wherein the second ratio of the channel width to the channel length is less than or approximately equal to the first ratio of the channel width to the channel length.

3. (Previously Presented) Power semiconductor according to claim 2, wherein the second ratio of the channel width to the channel length is at least a factor of 2 less than the first ratio of the channel width to the channel length.

4. (Currently Amended) Power semiconductor according to claim 1, wherein the first semiconductor region and the second semiconductor region intermesh~~, preferably~~ in finger-like fashion.

5. (Currently Amended) Power semiconductor according to claim 1, wherein the first semiconductor region is formed by the first channels, which are connected to the [[gate]] drive terminal of the field-effect power transistor, and the second semiconductor region is formed by the second channels, which lie between the first channels and are connected to the overvoltage protection device.

6. (Previously Presented) Power semiconductor according to claim 1, wherein the overvoltage protection device is provided in the form of a zener diode.

7. (Currently Amended) Power semiconductor according to claim 1, wherein the second channels are provided in strip-like fashion laterally separated by first channels~~, preferably~~ equidistantly.

8. (Previously Presented) Power semiconductor according to claim 1, wherein the first and second channels are patterned in the same way and/or embodied as trenches.

9. (Previously Presented) Power semiconductor according to claim 8, wherein the trenches are embodied with uniform oxide thickness.

10. (Previously Presented) Power semiconductor according to claim 8, wherein the trenches are embodied as field plate trenches.

11. (Previously Presented) Power semiconductor according to claim 1, wherein the first predetermined resistor is embodied between the two gate contacts as a polysilicon resistor.

12. (Previously Presented) Power semiconductor according to claim 1, wherein the first predetermined resistor is embodied between the two gate contacts as a trench poly-resistor, adjustable by way of the trench length, trench width and number of trenches.

13. (Previously Presented) Power semiconductor according to claim 1, wherein the first predetermined resistor is embodied as a semiconductor region with a predetermined dopant concentration.

14. (Previously Presented) Power semiconductor according to claim 1, wherein the value of the first predetermined resistor is dimensioned in a manner dependent on a gate resistor.

15. (Currently Amended) Power semiconductor according to claim 14, wherein the value of the first predetermined resistor lies in the range between 0.2 and 2 times the value of the gate resistor~~, preferably~~ between half the value of said gate resistor and the value of said gate resistor.

16. (Previously Presented) Power semiconductor according to claim 1, wherein a second predetermined resistor is provided between the drive terminal and the gate contact of the first semiconductor region.

17. (Previously Presented) Power semiconductor according to claim 16, wherein the second predetermined resistor is dimensioned in a manner dependent on the first predetermined resistor and the gate capacitances of the respectively adjoining gate contacts.

18. (Previously Presented) Power semiconductor according to claim 16, wherein the second predetermined resistor is dimensioned in such a way that the product of the first predetermined resistor and the gate capacitance of the second semiconductor region is approximately equal to the product of the second predetermined resistor and the gate capacitance of the first semiconductor region.